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- (71) Applicant (for all designated States except US): SHOWA DENKO K.K. [JP/JP]; 13-9, Shibadaimon 1-chome, Minato-ku, Tokyo 1058518 (JP).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): SAKURAI, Tetsuo [JP/JP]; c/o Showa Denko K.K., 1-1, Ohnodai 1-chome, Midori-ku, Chiba-shi, Chiba 2670056 (JP).
- (74) Agents: AOKI, Atsushi et al.; A. Aoki, Ishida & Associates, Toranomon 37 Mori Bldg., 5-1, Toranomon 3-chome, Minato-ku, Tokyo 1058423 (JP).

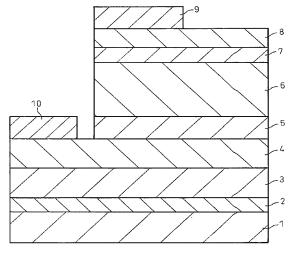
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(54) Title: GROUP III NITRIDE SEMICONDUCTOR DEVICE AND LIGHT-EMITTING DEVICE USING THE SAME



(57) Abstract: An object of the present invention is to provide a Group III nitride semiconductor device exhibiting improved crystallinity and a good performance. The inventive Group III nitride semiconductor device comprises a substrate, and a plurality of Group III nitride semiconductor layers provided on the substrate, wherein a first layer which is in contact with the substrate is composed of silicon-doped AlxGa1-xN ($0 \le x \le 1$). Also, the inventive Group III nitride semiconductor device comprises a substrate, and a plurality of Group III nitride semiconductor layers provided on the substrate, wherein a first layer which is in contact with the substrate is composed of AlxGa1-xN ($0 \le x \le 1$), and the difference in height between a protrusion and a depression which are present at the interface between the first layer and a second layer provided thereon is 10 nm or more and is equal to, or less than, 99% the thickness of the first layer.



